

OPTICAL DEVICES

Optical Devices

Mitsubishi Electric Optical Devices: The Key to Connecting Information Networks in the Future.

回天游 LASER DIODES FOR PROJECTORS Please visit our website for further details » なる(2)論 |回訳 19-638nm High-output Laser Diode for Projectors 520 0.8 Laser Display sRGB Compared to LEDs, semiconductor lasers have lower power consumption, higher output **500** 0.5 580 and can be used with optical systems having a higher maximum aperture. These considerable advantages mean that they can be used for projectors that do not require 0.4 • D65 focal adjustment. Mitsubishi Electric has a range of lasers available, including a 0.3 multi-mode semiconductor laser with a wavelength below 640nm and 3.8W output (when pulse-driven), 2.1W output (when CW-driven) that provides highly visible, vibrant red colors for color projectors. 0.1 0.3 0.4 0.5 0.6 0.7 0.8 Selection map of Red Laser Diodes ML562G86 **RED** [~640nm] ML562G85 ML562G84 ML562G75 Flat glass cap MI 562G86 [638nm, 3.8W(Pulse)] ML562G84 [638nm, 2.5W(Pulse)] ML501P73 ML501P73 Cap less [638nm, 1W(Pulse)] High Luminance ML562G85 CW [639nm, 2.1W(CW)] ML562G75 [636nm, 1.55W(CW)] ML520G73 Flat glass cap ML520G73 [638nm, 0.42W(CW)]

Line-up of Laser Diodes [Multi Transverse mode LD]

150

200

250

300

350

400

450

500 Luminous Flux [lm]

50

100

Type Number	Application	Wavelength [nm]	Output Power @CW [mW]	Output Power @Pulse [mW]	Case Temperature [°C]	Package
ML562G86	Display	638	-	3800	45	φ9.0mm TO Flat glass cap
ML562G84	Display	638	-	2500	45	φ9.0mm TO Flat glass cap
ML501P73	Display	638	500	1000	40	φ5.6mm TO Capless
ML562G85	Display	639	2100	-	45	φ9.0mm TO Flat glass cap
ML562G75	Display	636	1550	-	35	φ9.0mm TO Flat glass cap
ML520G73	Display	638	420	-	35	φ5.6mm TO Flat glass cap

OPTICAL DEVICES FOR OPTICAL COMMUNICATION SYSTEMS Please visit our website for further details

Optical Devices for Fiber-to-the-Home (FTTH)

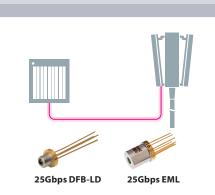
As streaming music and video becomes a common service, there is growing interest in Fiber-to-the-Home (FTTH), an optical communication system that provides high-speed, stable bandwidths to each household. Since approximately 2010, Mitsubishi Electric has contributed to FTTH by providing optical devices such as FP-LD, DFB-LD, EML and APD. Currently, 10G-EPON and XG-PON, which are faster communication systems, are being installed. For the future, the standardization of HS-PON as a next-generation FTTH system is also being discussed. Mitsubishi Electric maintains its lead in FTTH applications through its corresponding product lineup and new product development.

Optical Devices for Data Centers

Data centers have been expanding as a platform for storing and distributing digital contents such as SNS, photos, and videos on the ever-increasing Internet. In recent years, with the shift from on-premise-type to cloud-type storage, and the expansion of various cloud computing services, data centers are expected to grow as a platform that provides the foundation and infrastructure for cloud computing services. For the data center market, which requires advanced technologies, Mitsubishi Electric provides high-speed, low-power optical devices that contribute as the result of the unique characteristics of compound semiconductors.

Optical Devices for 5G Mobile Base Stations

Fifth-generation (5G) mobile communication system will offer ultrahigh-speed communication, low latency, and ultra-multiple connections. Accordingly, 5G mobile communication system is expected to become used widely around the world. With the increase in communication traffic, optical devices that support mobile base station networks are also required to operate at higher speeds, over a wider temperature range, and have higher reliability. Mitsubishi Electric utilizes the industry-standard T056 package to expand the connectivity of various products such as 25Gbps DFB and EML. We are also developing 100Gbps EML CAN for the future as well as services that will support the application and market growth of 5G mobile base stations, and is ready to support the market growth of 5G mobile base station applications in the future.



Upstream

* **E** : 2222222222222222222222

1.5µm band

DFB-LD or EML

133

同惑

1.3um band

FP-LD or DFB-LD, APD

1.3um band

DFB-LD or EML

Terminology

- APC ------ Angled Physical Contact
- APD ······ Avalanche Photo Diode
- APD TIA ------ Avalanche Photo Diode Trans Impedance Amplifier
- CPRI ----- Common Public Radio Interface
- CWDM ------ Coarse Wavelength Division Multiplexing
- DFB-LD ------ Distributed FeedBack Laser Diode
 DWDM ------- Dense Wavelength Division Multiplexing
- EAM ------ Electro Absorption Modulator
- EML ························Electro absorption Modulator integrated Laser diode
- ER -----Extended Reach
- FP-LD ········ Fabry-Perot Laser Diode
- FR ------ Fiber Reach
- FTTH ······Fiber To The Home

- G-PON
 Gigabit Passive Optical Network

 GE-PON
 Gigabit Ethernet Passive Optical Network

 HS-PON
 High-Speed Passive Optical Network

 LC
 Lucent Connector

 LED
 Light Emitting Diode

 LR
 Long Reach

 OLT
 Optical Line Terminal

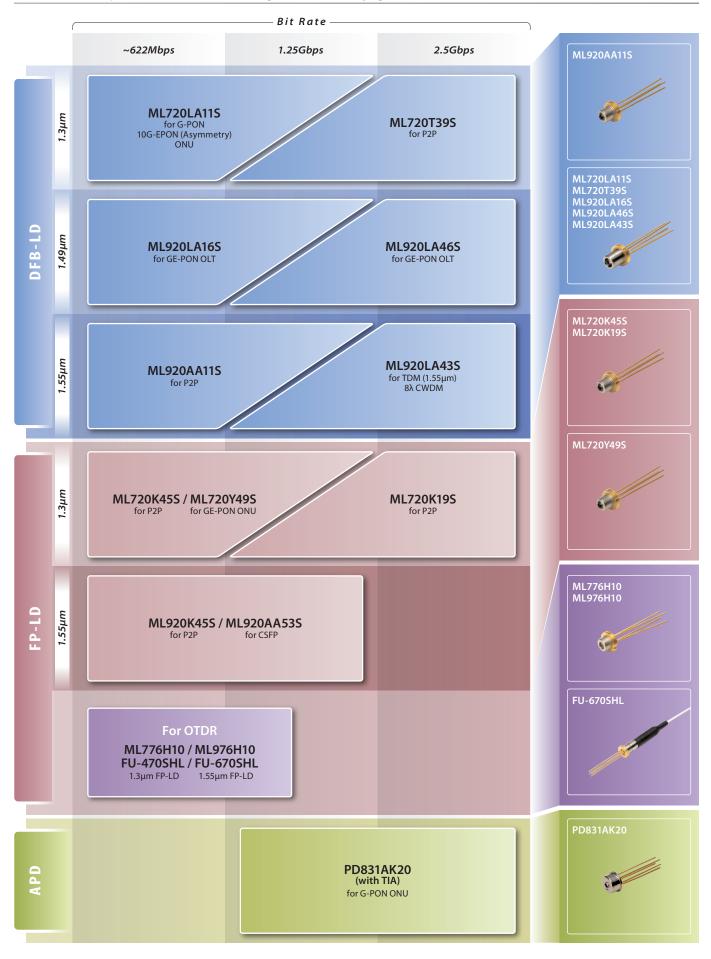
 ONU
 Optical Network Unit

 OTDR
 Optical Time Domain Reflectometer

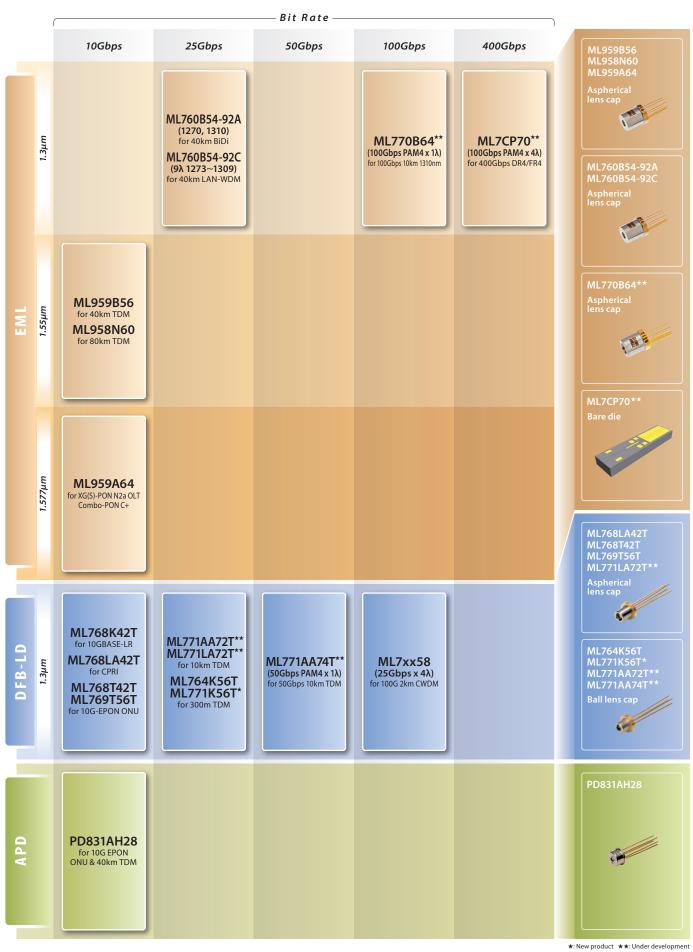
 P2P
 Peer to Peer
 - PAM4 ······· 4-level pulse amplitude modulation
 - PC ----- Physical Contact
 - PD-TIA ------ Photo Diode with Trans-Impedance Amplifier

RoF	Radio over Fiber
ROSA	Receiver Optical Sub-Assembly
SC	Single fiber Connector
SDH	- Synchronous Digital Hierarchy
SFP+	• Small Form-factor Pluggable Plus
SONET ······	Synchronous Optical NETwork
TOSA	Transmitter Optical Sub-Assembly
VSR	Very Short Reach
XFP	• 10 Gigabit small Form-factor Pluggable
10G-EPON	 10 Gigabit Ethernet Passive Optical Network
XG-PON	10 Gigabit Passive Optical Network
XMD-MSA ····	• 10 Gbps Miniature Device Multi Source Agreement

Selection Map of OPTICAL DEVICES [Under 2.5Gbps]



Selection Map of OPTICAL DEVICES [Over 10Gbps]



	Type Number	Chip Type	Package	Wavelength [nm]	Case Temp. [°C]	Features
	ML720T39S	DFB-LD	TO56-CAN	1310	-40~+95	P2P
	ML720K19S	FP-LD	TO56-CAN	1310	-40~+85	P2P
2.5G	ML920LA46S	DFB-LD	TO56-CAN	1490	-40~+85	G-PON OLT
	ML920LA43S	DFB-LD	TO56-CAN	1550	-20~+95	P2P
	ML920LA43S	DFB-LD	TO56-CAN	1470~1610 8λ CWDM	-10~+85	8λ CWDM
	ML720LA11S	DFB-LD	TO56-CAN	1310	-40~+85	G-PON ONU, 10G-EPON (Asymmetry) ONU
	ML720K45S	FP-LD	TO56-CAN	1310	-40~+85	P2P
	ML720Y49S	FP-LD	TO56-CAN	1310	-40~+85	GE-PON ONU, High coupling efficiency
1.25G/ ~622M	ML920LA16S	DFB-LD	TO56-CAN	1490	-40~+85	GE-PON OLT
	ML920AA11S	DFB-LD	TO56-CAN	1550	-40~+85	P2P
	ML920K45S	FP-LD	TO56-CAN	1550	-40~+85	P2P
	ML920AA53S	FP-LD	TO56-CAN	1530	-40~+95	P2P, CSFP
	FU-470SHL	FP-LD	Coaxial Pigtail	1310	-20~+70	OTDR
For	FU-670SHL	FP-LD	Coaxial Pigtail	1550	-20~+70	OTDR
OTDR	ML776H10	FP-LD	TO56-CAN	1310	-40~+85	OTDR
	ML976H10	FP-LD	TO56-CAN	1550	-40~+85	OTDR

Line Up of LD / LD Modules [Under 2.5Gbps]

Line Up of APD [Under 2.5Gbps]

	Type Number	Chip Type	Package	Wavelength [nm]	Case Temp. [°C]	Features
2.5G	PD831AK20	APD	TO46-CAN	1490	-40~+85	Built-in TIA, G-PON ONU

SAFETY CAUTIONS FOR USE OR DISPOSAL OF LISTED PRODUCTS -

The warnings below apply to all products listed in this pamphlet.

	WARNING			
Laser Beam	While the laser diode is on, its gives a laser beam. Even if we can't see a laser beam by its wavelengt, penetration into the eye by a laser beam or its reflected light may cause eye injury. Prevent the irradiating part or its reflected light from entering the eyes.			
Injury	Fiber fragments may cause injury. In cases of fiber bending or breakage, never touch the fragment.			
GaAs	Gallium arsenide (GaAs) is used in these products. To avoid danger, strictly observe the following cautions. • Never place the products in your mouth. • Never burn or break the products, or use any type of chemical treatment to reduce them to gas or powder. • When disposing of the products, always follow the laws which apply, as well as your own company's internal waste treatment regulations.			
Disposal of Flame-Retarded Fiber Core Wire	Flame retardant resin must be disposed of according to law of industrial waste in disposal place. This product is a bromine type flame-retarded resin, containing bromine compounds and antimony trioxide. All disposal operations should be conducted with full consideration of this content.			

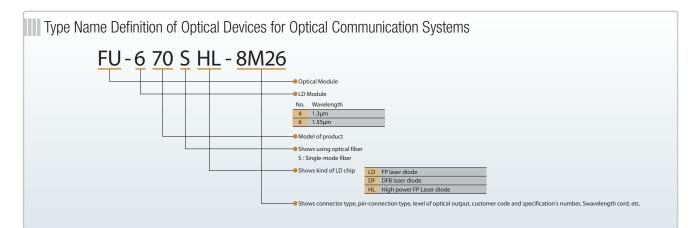
Line Up of LD / LD Modules [Over 10Gbps]

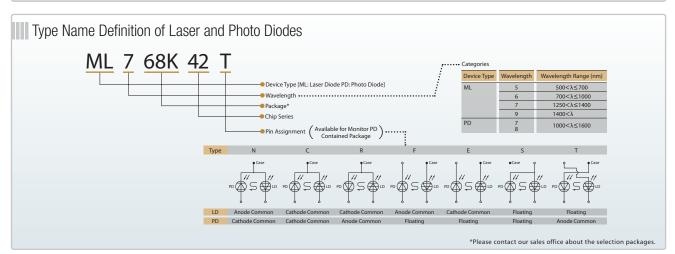
	Type Number	Chip Type	Package	Wavelength [nm]	Case Temp. [°C]	Features
400G	ML7CP70**	5141		1310	+5~+85	100Gbps, PAM4, 400G DR4
400G		EML	Bare die	4λ CWDM	+25~+75	100Gbps x 4λ, PAM4, 400G FR4
100G	ML770B64**	EML	TO56-CAN	1310	-5~+80	100Gbps x 1λ, PAM4, 10km
1000	ML7xx58	DFB-LD	TBD	4λ CWDM	+20~+70	25Gbps x 4λ
50G	ML771AA74T**	DFB-LD	TO56-CAN	1310	-40~+90	50Gbps, PAM4, 10km, (Df=6.6mm)
	ML760B54-92A	EML	TO56-CAN	1270 , 1310	-40~+95	Bidirectional, 25Gbps, SFP28, 40km
	ML760B54-92C	EML	TO56-CAN	9λ 1273~1309	-40~+95	25Gbps, SFP28, 40km
25G	ML764K56T	DFB-LD	TO56-CAN	1310	-40~+90	25Gbps, SFP28, 300m (Df=5.8mm)
250	ML771K56T*	DFB-LD	TO56-CAN	1310	-40~+90	25Gbps, SFP28, 300m, (Df=5.8mm)
	ML771AA72T**	DFB-LD	TO56-CAN	1310	-40~+90	25Gbps, SFP28, 10km, (Df=6.6mm)
	ML771LA72T**	DFB-LD	TO56-CAN	1270, 1310, 1330	-40~+90	25Gbps, SFP28, 10km, (Df=7.5mm)
	ML959B56	EML	TO56-CAN	1550	-5~+80	XFP/SFP+ 40km
	ML958N60	EML	TO56-CAN	1550	-5~+80	XFP/SFP+ 80km
	ML959A64	EML	TO56-CAN	1577	-5~+80	XG(S)-PON N2a OLT
10G	ML768K42T	DFB-LD	TO56-CAN	1310	-40~+95	10GBASE-LR, SONET/SDH
	ML768LA42T	DFB-LD	TO56-CAN	1270, 1330	-40~+95	CPRI
	ML768T42T	DFB-LD	TO56-CAN	1270	-5~+75	10G-EPON (Symmetry) ONU
	ML769T56T	DFB-LD	TO56-CAN	1270	-40~+90	10G-EPON ONU (Df=10.1mm)

★: New product ★★: Under development

Line Up of APD / APD Modules [Over 10Gbps]

	Type Number	Chip Type	Package	Wavelength [nm]	Case Temp. [°C]	Features
10G	PD831AH28	APD	TO46-CAN	1310 / 1577	-40~+90	Built-in TIA, 10G-EPON/XG-PON ONU & 40km





Mitsubishi Electric Semiconductors & Devices Website

www.MitsubishiElectric.com/semiconductors/



Keep safety first in your circuit designs!

Mitsubishi Electric Corporation puts the maximum effort into making semiconductor products better and more reliable, but there is always the possibility that trouble may occur with them. Trouble with semiconductors may lead to personal injury, fire or property damage. Remember to give due consideration to safety when making your circuit designs, with appropriate measures such as (i) placement of substitutive, auxiliary circuits, (ii) use of non-flammable material or (iii) prevention against any malfunction or mishap.

Notes regarding these materials -

- .

- Notes regarding these materials
 These materials
 These materials are intended as a reference to assist our customers in the selection of the Mitsubishi Electric Semiconductor product best suited to the customer's application; they do not convey any license under any intellectual
 property rights, or any other rights, belonging to Mitsubishi Electric Corporation or a third party.
 Mitsubishi Electric Corporation assumes no responsibility for any damage, or infringement of any third-party's rights, originating in the use of any product data, diagrams, charts, programs, algorithms, or circuit application examples
 contained in these materials.
 All information contained in these materials, including product data, diagrams, charts, programs and algorithms represents information on products at the time of publication of these materials, and are subject to change by Mitsubishi
 Electric Corporation without notice due to product improvements or other reasons. It is therefore recommended that customers contact Mitsubishi Electric Corporation or an authorized Mitsubishi Electric Semiconductor product
 distributor for the latest product information before purchasing a product listed herein.
 The information described here may contained in the end are materials, including product data, diagrams, charts, programs, and algorithms, please be sure to evaluate all information as total system before making a final decision on
 the applicability of the information ontained in these materials, including product data, diagrams, charts, programs, and algorithms, please be sure to evaluate all information contained thereins
 there any contained in the effort and products. Mitsubishi Electric Corporation by any and angle, please be sure to evaluate all information as total system before making a final decision on
 the applicability of the information contained there and that using the information contained herein.
 Mitsubishi Electric Corporation semiconductory are not designed or manufact
- .

- Any diversion or re-export contrary to the export control laws and regulations of Japan and/or the country of destination is prohibited. Please contact Mitsubishi Electric Corporation or an authorized Mitsubishi Electric Semiconductor product distributor for further details on these materials or the products contained therein.

MITSUBISHI ELECTRIC CORPORATION

HEAD OFFICE: TOKYO BLDG., 2-7-3, MARUNOUCHI, CHIYODA-KU, TOKYO 100-8310, JAPAN www.MitsubishiElectric.com